

**IN THE CLAIMS:**

Please amend the claims as follows:

Claims 1-9 (Canceled).

Claim 10 (Previously Presented): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light while positioning a light-converging point therewithin, so as to form a modified region due to multiphoton absorption within the object, and causing the modified region to form a starting point region for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and

a pressing step of pressing the object from the other end face side of the object.

Claim 11 (Previously Presented): A method of cutting an object to be processed according to claim 10, wherein the object is pressed along the line along which the object should be cut in the pressing step.

Claim 12 (Previously Presented): A method of cutting an object to be processed according to claim 11, wherein positional data of the line along which the object should be cut with respect to the object is stored in the starting point region for cutting forming step; and

wherein the object is pressed along the line along which the object should be cut according to the positional data in the pressing step.

Claim 13 (Previously Presented): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1  $\mu$ s or less, so as to form a modified region including a crack region within the object, and causing the modified region to form a starting point region for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and

a pressing step of pressing the object from the other end face side of the object.

Claim 14 (Previously Presented): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1  $\mu$ s or less, so as to form a modified region including a molten processed region within the object, and causing the modified region to form a starting point region for

cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and  
a pressing step of pressing the object from the other end face side of the object.

Claim 15 (Previously Presented): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1 ns or less, so as to form a modified region including a refractive index change region which is a region with a changed refractive index within the object, and causing the modified region to form a starting point region for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and

a pressing step of pressing the object from the other end face side of the object.

Claim 16 (Currently Amended): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed which is made of a semiconductor material with laser light while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1  $\mu$ s or less, so as to form a modified

region within the object, and causing the modified region to form a starting point region for cutting, deviated from a ~~center~~ center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and a pressing step of pressing the object from the other end face side of the object.

Claim 17 (Previously Presented): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed which is made of a piezoelectric material with laser light while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1  $\mu$ s or less, so as to form a modified region within the object, and causing the modified region to form a starting point region for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and a pressing step of pressing the object from the other end face side of the object.

Claim 18 (Currently Amended): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed which is made of a semiconductor material with laser light while positioning a light-converging point within the object, so as to form a molten processed region within the object, and causing the molten processed region to form a starting point region for cutting, deviated

from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along ~~with~~ which the object should be cut in the object; and

a pressing step of pressing the object from the other end face side of the object.

Claim 19 (Previously Presented): A method of cutting an object to be processed according to claim 10, wherein a plurality of functional devices are formed on the other end face, the object is pressed from the other end face side by pressing means along the line along which the object should be cut and which is set to pass between the functional devices adjacent each other in the pressing step.

Claim 20 (Previously Presented): A method of cutting an object to be processed according to claim 19, wherein the object is pressed from the other end face side by pressing means by way of a protective film attached to the other end face in the pressing step.

Claim 21 (Previously Presented): A method of cutting an object to be processed according to claim 19, wherein an expansion film is attached to the one end face in the pressing step.

Claim 22 (Previously Presented): A method of cutting an object to be processed according to claim 10, wherein a plurality of functional devices are formed on the one end face, the object is pressed from the other end face side by pressing means along the line along which

the object should be cut and which is set to pass between the functional devices adjacent each other in the pressing step.

Claim 23 (Previously Presented): A method of cutting an object to be processed according to claim 22, wherein the object is pressed from the other end face side by pressing means by way of an expansion film attached to the other end face in the pressing step.

Claim 24 (New): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point therewithin, so as to form a modified region due to multiphoton absorption within the object, with the modified region forming a starting point region serving as a starting point for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such pressing thereby resulting in cutting the object along the line along which the object is to be cut in order to provide at least one manufactured semiconductor device.

Claim 25 (New): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1  $\mu$ s or less, so as to form a modified region including a crack region within the object, with the modified region forming a starting point region serving as a starting point for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such pressing thereby resulting in cutting the object along the line along which the object is to be cut in order to provide at least one manufactured semiconductor device.

Claim 26 (New): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1  $\mu$ s or less, so as to form a modified region including a molten processed region within the object, with the modified region forming a starting point region serving as a starting point for cutting, deviated from a center position of the object in a

thickness direction thereof toward one end face of the object, the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such pressing thereby resulting in cutting the object along the line along which the object is to be cut in order to provide at least one manufactured semiconductor device.

Claim 27 (New): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1 ns or less, so as to form a modified region including a refractive index change region which is a region with a changed refractive index within the object, with the modified region forming a starting point region serving as a starting point for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such pressing thereby resulting in cutting the object along the line along which the object is to be cut in order to provide at least one manufactured semiconductor device.



Claim 28 (New): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising a semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point within the object under a condition with a peak power density of at least  $1 \times 10^8$  (W/cm<sup>2</sup>) at the light-converging point and a pulse width of 1  $\mu$ s or less, so as to form a modified region within the object, with the modified region forming a starting point region serving as a starting point for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such pressing thereby resulting in cutting the object along the line along which the object is to be cut in order to provide at least one manufactured semiconductor device.

Claim 29 (New): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising a semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point within the object, so as to form a molten processed region within the object, with the molten processed region forming a starting point region serving as a starting point for cutting, deviated from a

center position of the object in a thickness direction thereof toward one end face of the object,  
the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such  
pressing thereby resulting in cutting the object along the line along which the object is to be cut  
in order to provide at least one manufactured semiconductor device.